SUBJECT AREAS:
MAGNETIC DEVICES
ELECTRICAL AND ELECTRONIC
ENGINEERING

CORRIGENDUM: An error-resilient non-volatile magneto-elastic universal logic gate with ultralow energy-delay product

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SCIENTIFIC REPORTS:

4 : 7553
DOI: 10.1038/srep07553
(2014)

Published:
23 December 2014

Updated:
13 March 2015

This Article contains typographical errors in the Introduction section.

“The resistance of the MTJ then drops by $\sim 50\%$ since the resistance is approximately proportional to $\cos^2(\gamma/2)$, where γ is the angle between the magnetizations of the top and bottom magnets, assuming that the spin injection and detection efficiencies of the magnet-spacer interfaces are $\sim 100\%$ ²² [if the efficiencies are less than 100%, the logic levels will be encoded in V_0 and xV_0 , where $x > 0.5$]”

should read:

“The resistance of the MTJ then drops by $\sim 50\%$ since the resistance is inversely proportional to $1 + \eta_1\eta_2\cos\gamma$, where γ is the angle between the magnetizations of the top and bottom magnets²², assuming that the spin injection and detection efficiencies of the magnet-spacer interfaces η_1 and η_2 are $\sim 70\%$ [if the efficiencies are less than 70%, the logic levels will be encoded in V_0 and xV_0 , where $x > 0.5$]”